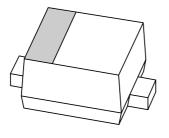
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG3002AEBLow V_F MEGA Schottky barrier diode

Product specification

2002 May 06





Low V_F MEGA Schottky barrier diode

PMEG3002AEB

FEATURES

Forward current: 0.2 AReverse voltage: 30 V

Very low forward voltage

• Ultra small SMD package.

APPLICATIONS

• Ultra high-speed switching

• High efficiency DC/DC conversion

· Voltage clamping

• Inverse-polarity protection

· Low voltage rectification

• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION	
1	cathode	
2	anode	

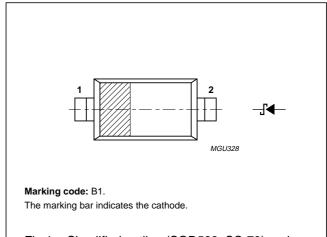


Fig.1 Simplified outline (SOD523; SC-79) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
V_R	continuous reverse voltage		_	30	V	
I _F	continuous forward current		_	200	mA	
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA	
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms half sinewave; JEDEC method	_	1	A	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	125	°C	
T _{amb}	operating ambient temperature		-65	+125	°C	

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	see Fig.2			
		I _F = 0.1 mA	130	190	mV
		I _F = 1 mA	190	250	mV
		I _F = 10 mA	255	300	mV
		I _F = 100 mA	355	400	mV
		I _F = 200 mA	420	480	mV
I _R	continuous reverse current	V _R = 10 V; see Fig.3; note 1	2.5	10	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$; see Fig.4	20	25	pF

Note

1. Pulsed test: $t_p = 300 \ \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	450	K/W

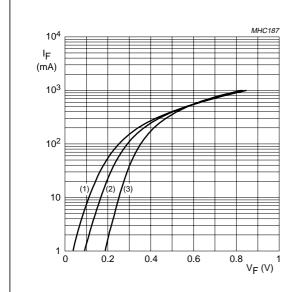
Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

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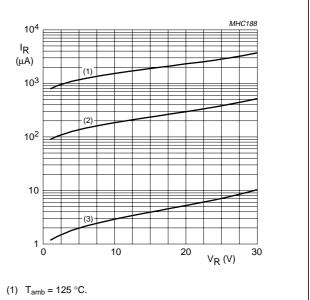
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GRAPHICAL DATA



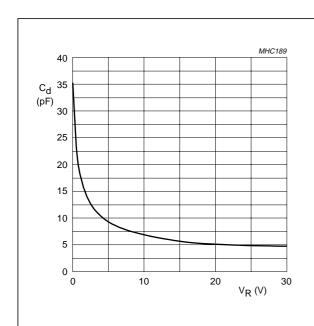
- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}.$

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

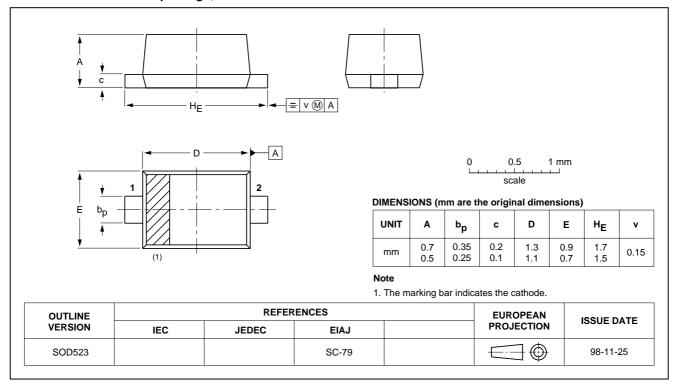
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

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